2SB1026

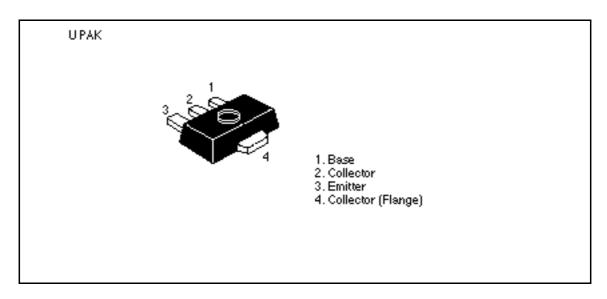
Silicon PNP Epitaxial

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Application

- Low frequency power amplifier
- Complementary pair with 2SD1419

Outline





2SB1026

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V _{CEO}	-100	V
Emitter to base voltage	V_{EBO}	– 5	V
Collector current	I _c	– 1	А
Collector peak current	i _{C(peak)} *1	-2	А
Collector power dissipation	P _C *2	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10 ms, Duty cycle 20%

2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

Electrical Characteristics ($Ta = 25^{\circ}C$)

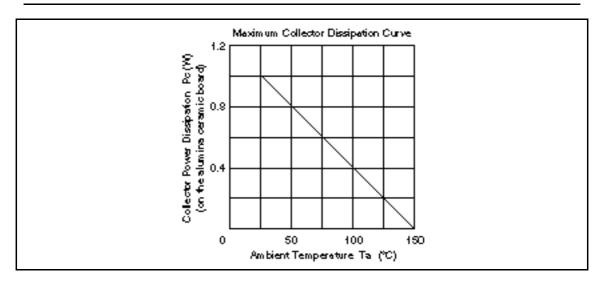
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-100	_	_	V	$I_C = -1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 5	_	_	V	$I_{E} = -10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	-10	μΑ	$V_{CB} = -100 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE1} *1	60	_	200		$V_{CE} = -5 \text{ V}, I_{C} = -150 \text{ mA}$
	h _{FE2}	30	_	_		$V_{CE} = -5 \text{ V},$ $I_{C} = -500 \text{ mA (Pulse test)}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	– 1	V	$I_{\rm C} = -500 \text{ mA},$ $I_{\rm B} = -50 \text{ mA} \text{ (Pulse test)}$
Base to emitter voltage	V_{BE}	_	_	-0.9	V	$V_{CE} = -5 \text{ V}, I_{C} = -150 \text{ mA}$
Gain bandwidth product	f_{T}	_	140	_	MHz	$V_{CE} = -5 \text{ V}, I_{C} = -150 \text{ mA}$
Collector output capacitance	Cob	_	20	_	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz

Note: 1. The 2SB1026 is grouped by h_{FE1} as follows.

Mark	DL	DM
h _{FE1}	60 to 120	100 to 200

See characteristic curves of 2SB1025.

2SB1026



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